

Electrically Protected Valley-Orbit Qubit in Silicon

- FAM talk -

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XI. Jahrgang.

August 1891.

Achtes Heft.

Ein neuer Interferenzrefraktor.

Von
Dr. L. Zehnder in Basel.

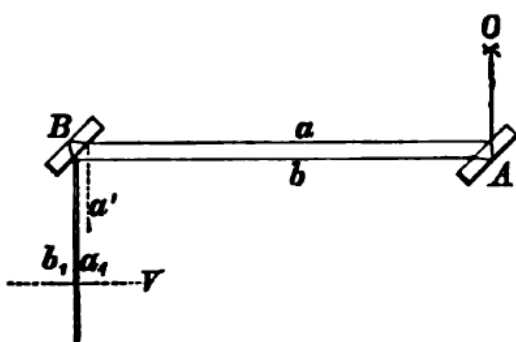


Fig. 1.

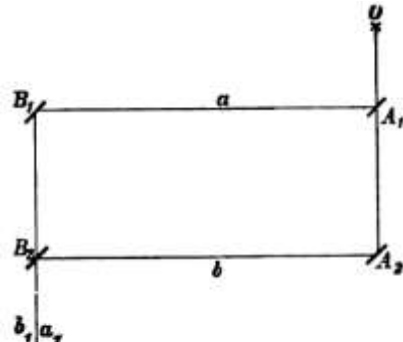


Fig. 2.

Ueber einen Interferenzrefraktor.

Von
Ludwig Mach in Prag.

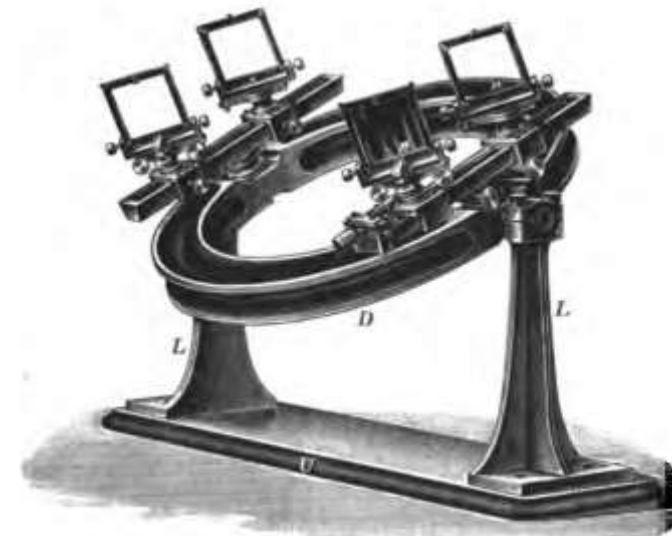


Fig. 1.

1) Den hier beschriebenen Apparat hatte ich bereits Ende Juli 1891 in seinen Theilen fertiggestellt, konnte jedoch denselben wegen verspäteter Lieferung einer Werkzeugmaschine erst Anfang November 1891 ganz vollenden. — Vergl. die vorläufige Mittheilung im *Anzeiger der Wiener Akademie* vom 5. November 1891.

[1] Zehnder, L., *Zeitschrift für Instrumentenkunde*. 11: 275–285 (1861)

[2] Mach, L., *Zeitschrift für Instrumentenkunde*. 12: 89–93 (1862)

- electrical fluctuations are omnipresent
- source of decoherence

- reduce and mitigate charge noise
 - operation at sweet spot
 - dynamic decoupling
 - hybrid qubits

- in Si: Valley-Orbit Qubit?
 - analogon to transmon qubit





Theory of LZSM
interferometry

Device

Example of
Application

Summary and
Outlook

X. Mi, S. Kohler, J. R. Petta, arXiv:1805.04545



Quantum Two Level System

- Hamiltonian of two level system (TLS):

$$H(t) = -\frac{\Delta}{2}\sigma_x - \frac{\varepsilon(t)}{2}\sigma_z$$

- eigenstates

$$E_{\pm} = \pm\frac{1}{2}\Omega(t)$$

$$\Omega(t) = \sqrt{\Delta^2 + \varepsilon(t)^2}$$

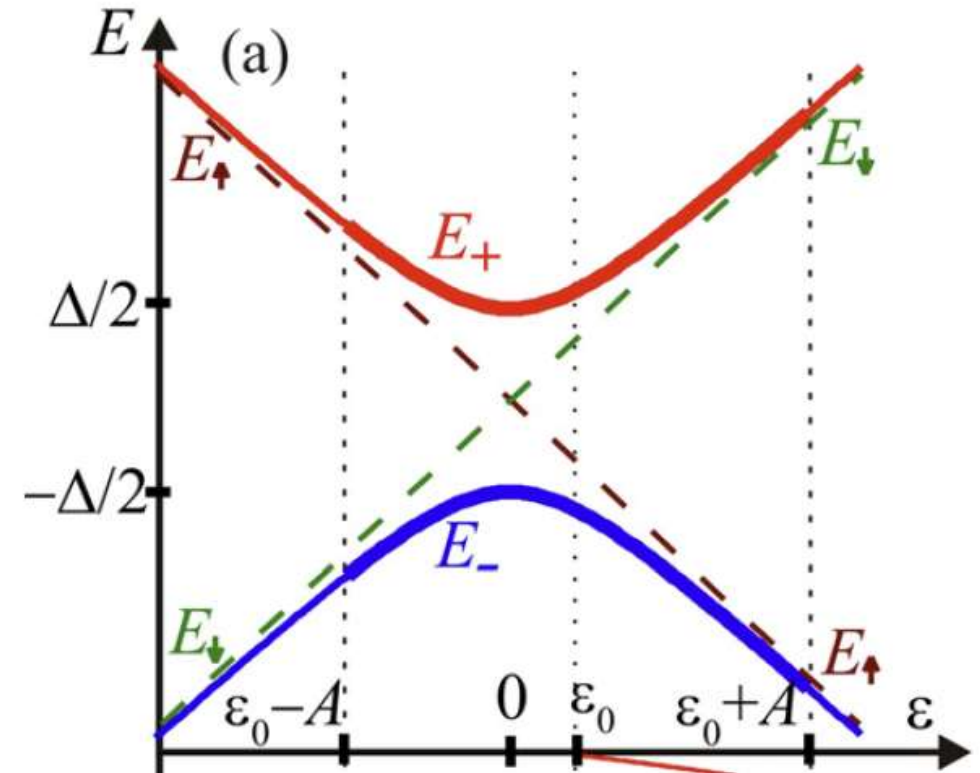


Fig: Energy levels versus detuning with avoided crossing between the two eigenstates ^[1]

[1] Shevchenko, S. N., Ashab, S., Nori, F., Phys. Rep. 492, 1 (2010)

Landau-Zehner Transition

- *single* passage across avoided crossing
- assume monochromatic drive

$$\varepsilon(t) = \varepsilon_0 + A \cdot \sin(\omega t)$$

- transition probability

$$P_{LZ} = \exp\left(-2\pi \frac{\Delta^2}{4v}\right)$$

- acquire Stokes phase during non-adiabatic transition

$$\varphi_S = \frac{\pi}{4} + \delta(\ln \delta - 1) + \arg \Gamma(1 - i\delta)$$

$$\delta = \frac{\Delta^2}{4v}$$

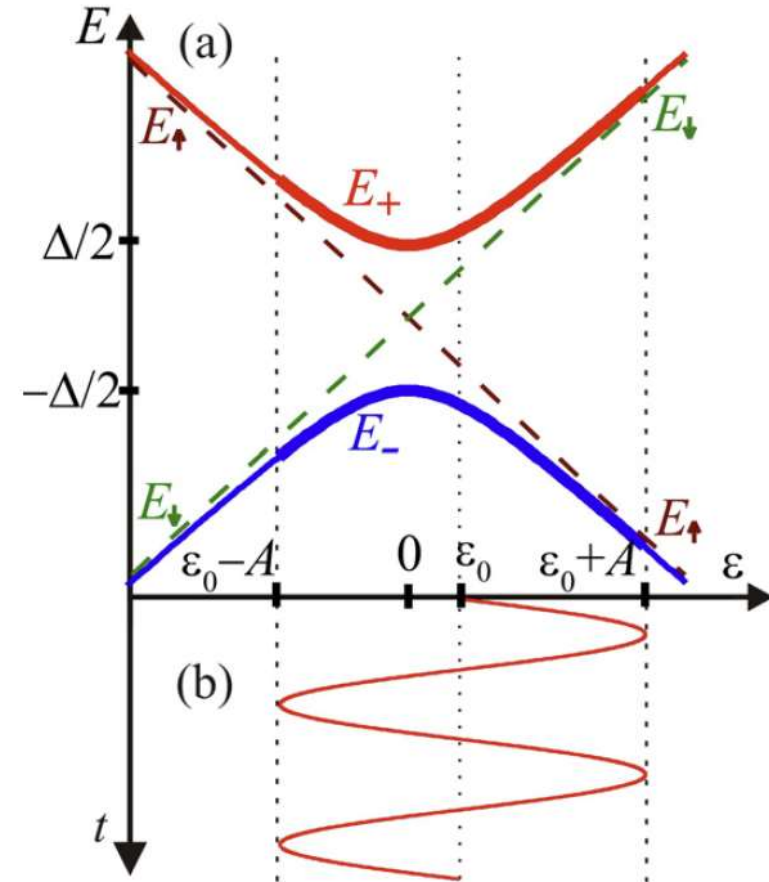


Fig: Energy levels versus detuning with avoided crossing between the two eigenstates ^[1]

[1] Shevchenko, S. N., Ashab, S., Nori, F., Phys. Rep. 492, 1 (2010)

Stückelberg Phase

- *double* passage across avoided crossing
- probability to end up in upper level

$$P_+ = 4P_{LZ}(1 - P_{LZ}) \sin^2 \Phi_{St}$$

- with the Stückelberg phase

$$\Phi_{St} = \zeta_2 + \phi_S$$

- ζ_2 phase acquired during adiabatic evolution
- ϕ_S phase acquired during non-adiabatic transitions (Stokes phase)

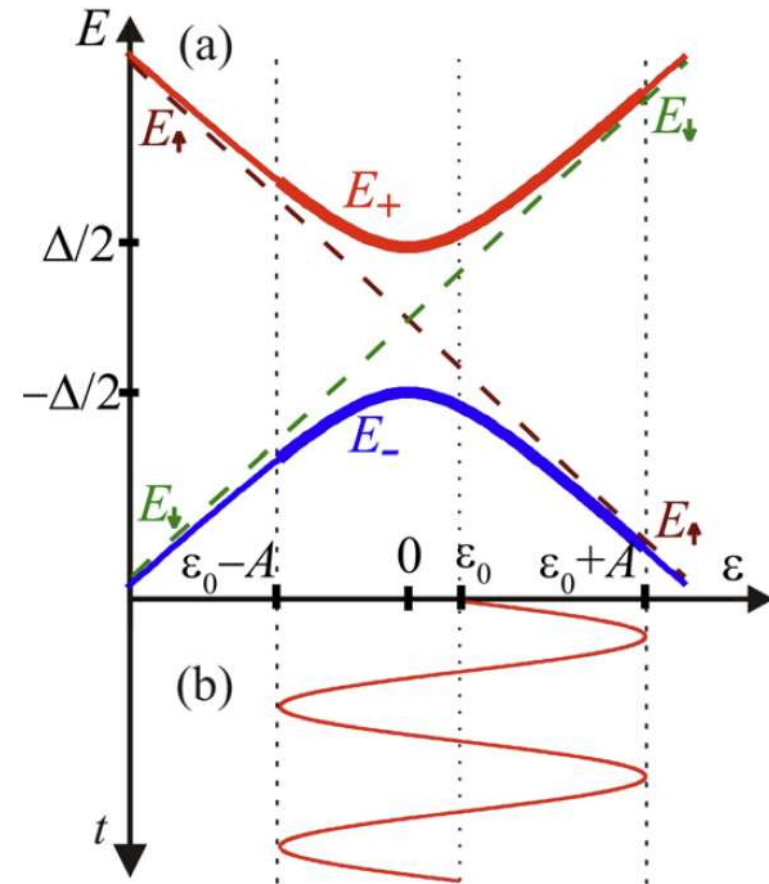


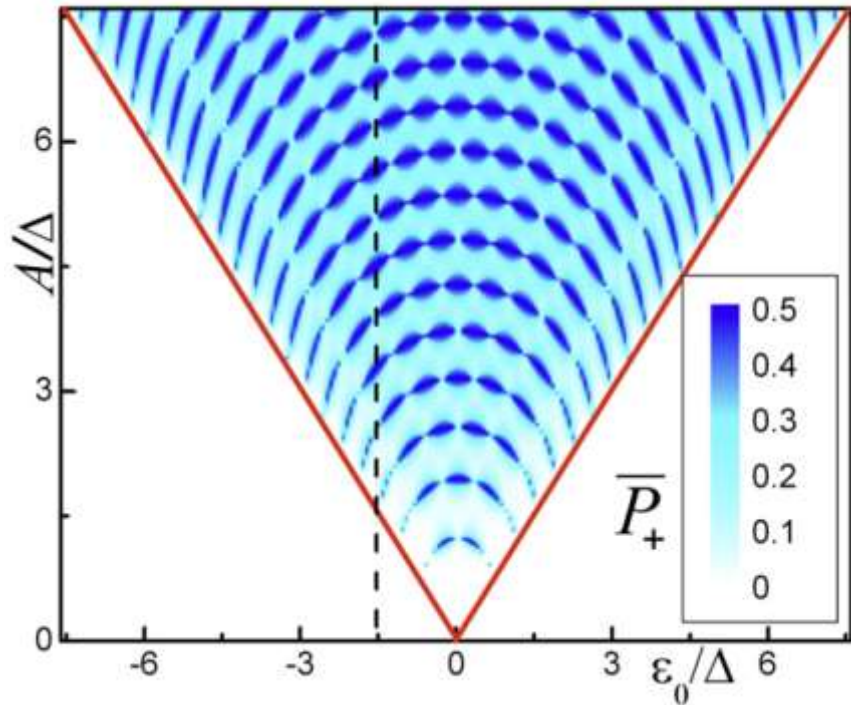
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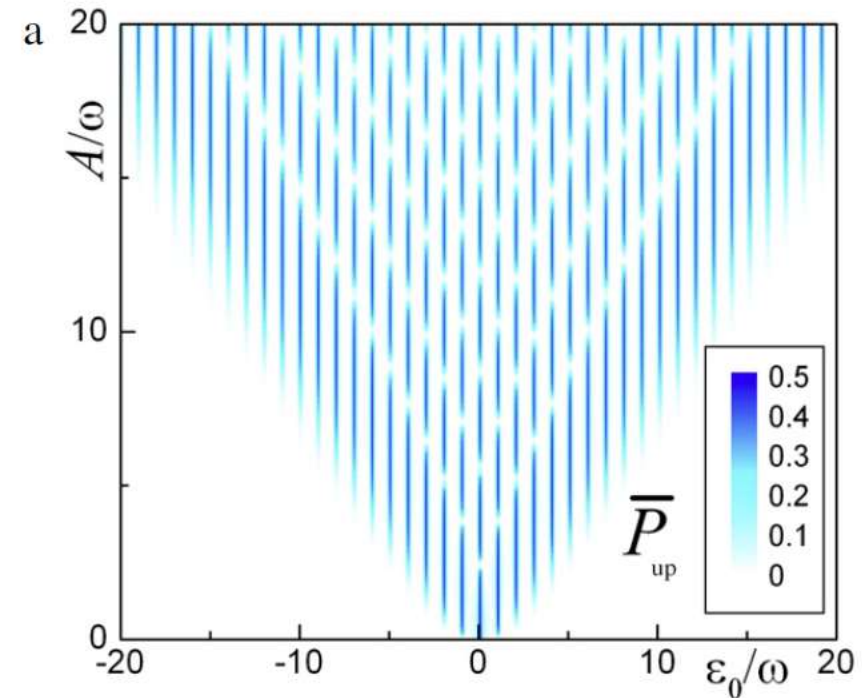
Landau-Zehner-Stückelberg-Majorana Interferometry

- *multiple* passage across avoided crossing

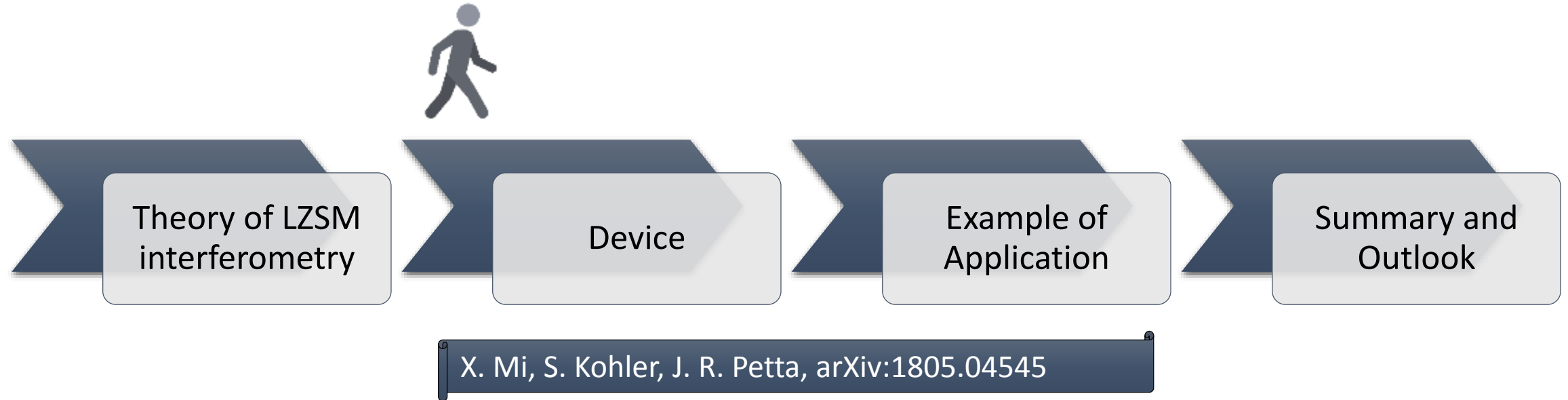
Slow passage limit



Fast passage limit



[1] Shevchenko, S. N., Ashab, S., Nori, F., Phys. Rep. 492, 1 (2010)



Device Overview

- Si/SiGe double quantum dot in single electron regime
- coupled to microwave cavity
 - **strong coupling regime**
 - $\kappa/2\pi = 3.3$ MHz
 - $\gamma/2\pi = 4.1$ MHz
 - $2g_{\text{VO}}/2\pi = 16.0$ MHz
- hybrid valley-orbit state
 - strain lifts 6-fold valley degeneracy
 - $E_L = 37.5$ μeV , $E_R = 38.3$ μeV

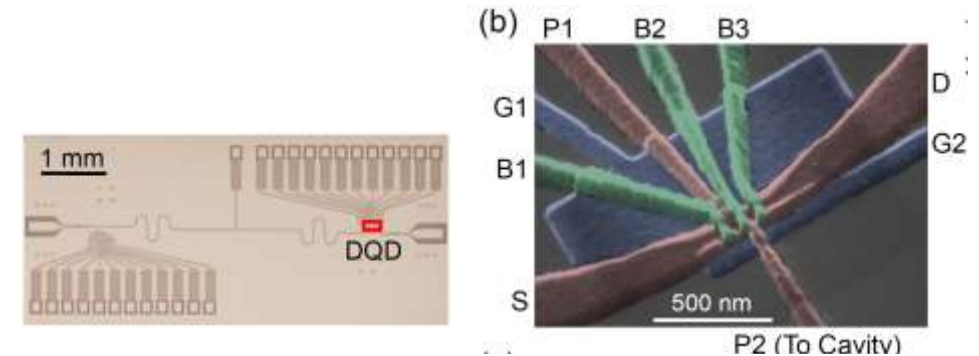


Fig: Optical image and colored SEM image of the device; cavity frequency $f_c = 7.796$ GHz ^[1]

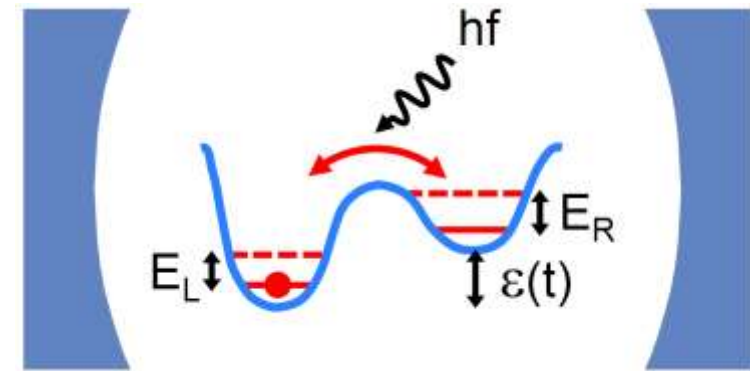
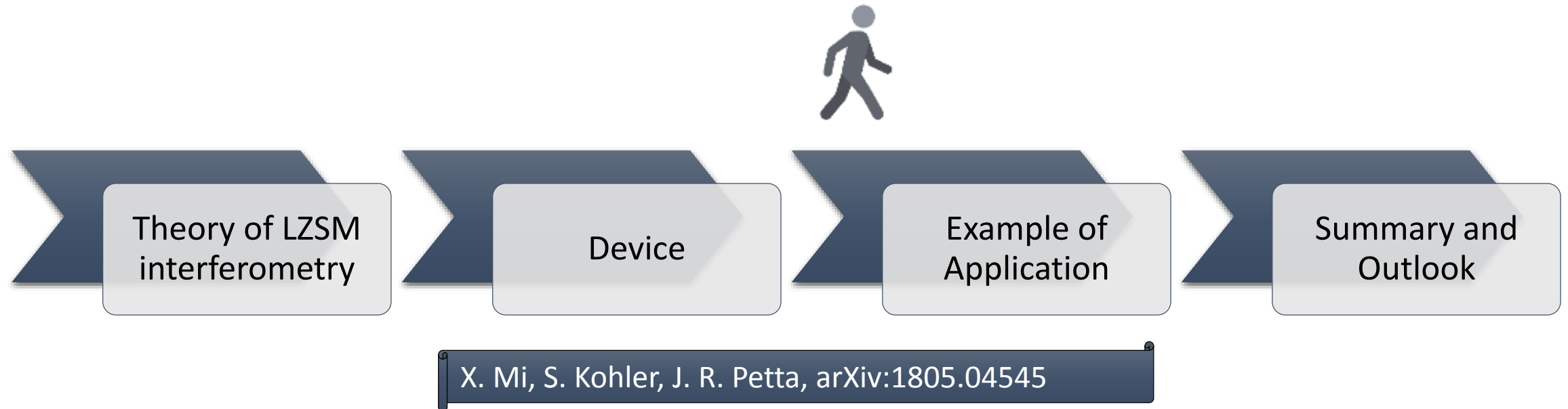


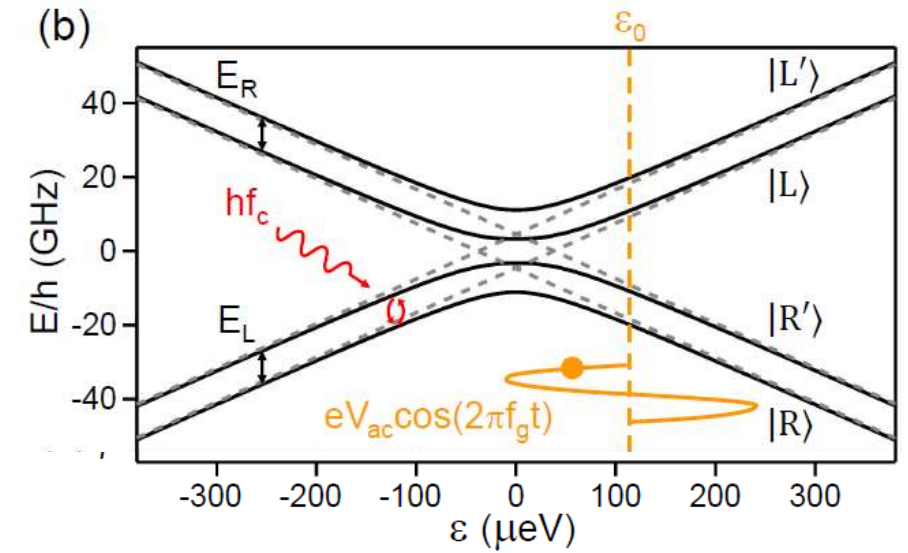
Fig: Schematic displaying the DQD in the cavity with tunable detuning $\epsilon(t)$ and cavity photon hf ^[1]

[1] Mi, X., Kohler, S., Petta, J. R., arXiv:1805.04545



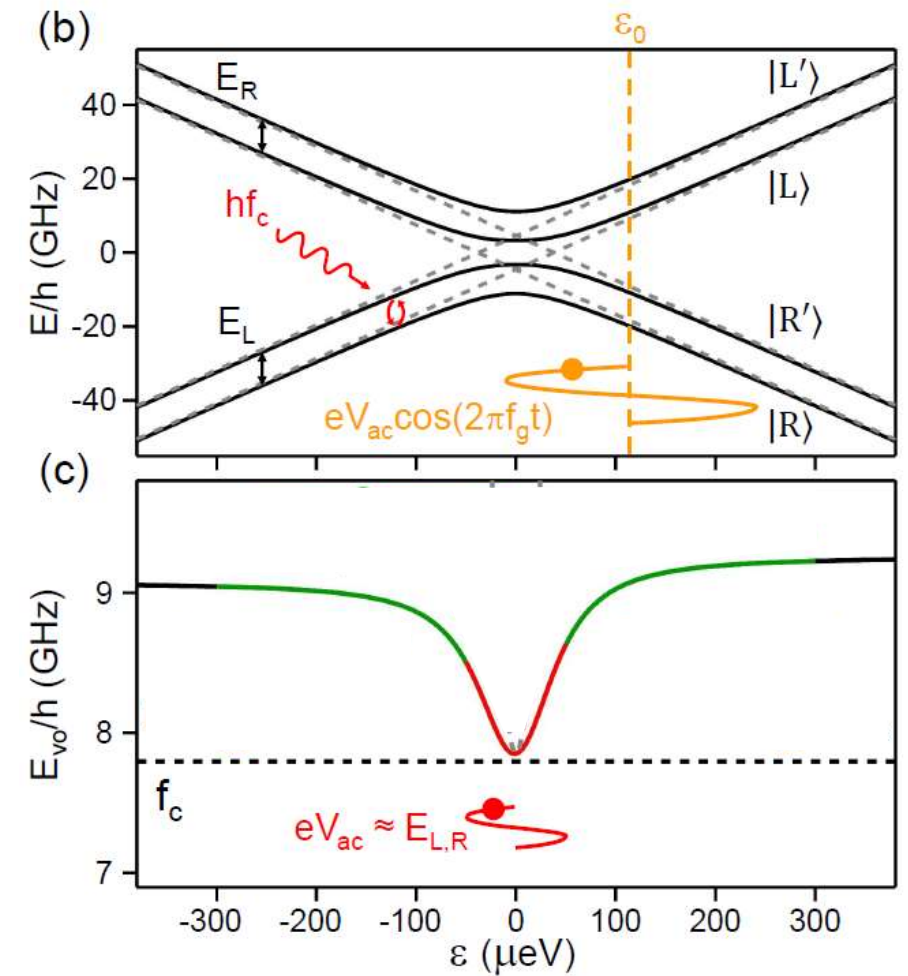
Landau-Zehner-Stückelberg-Majorana Interferometry

- DQD energy level diagram



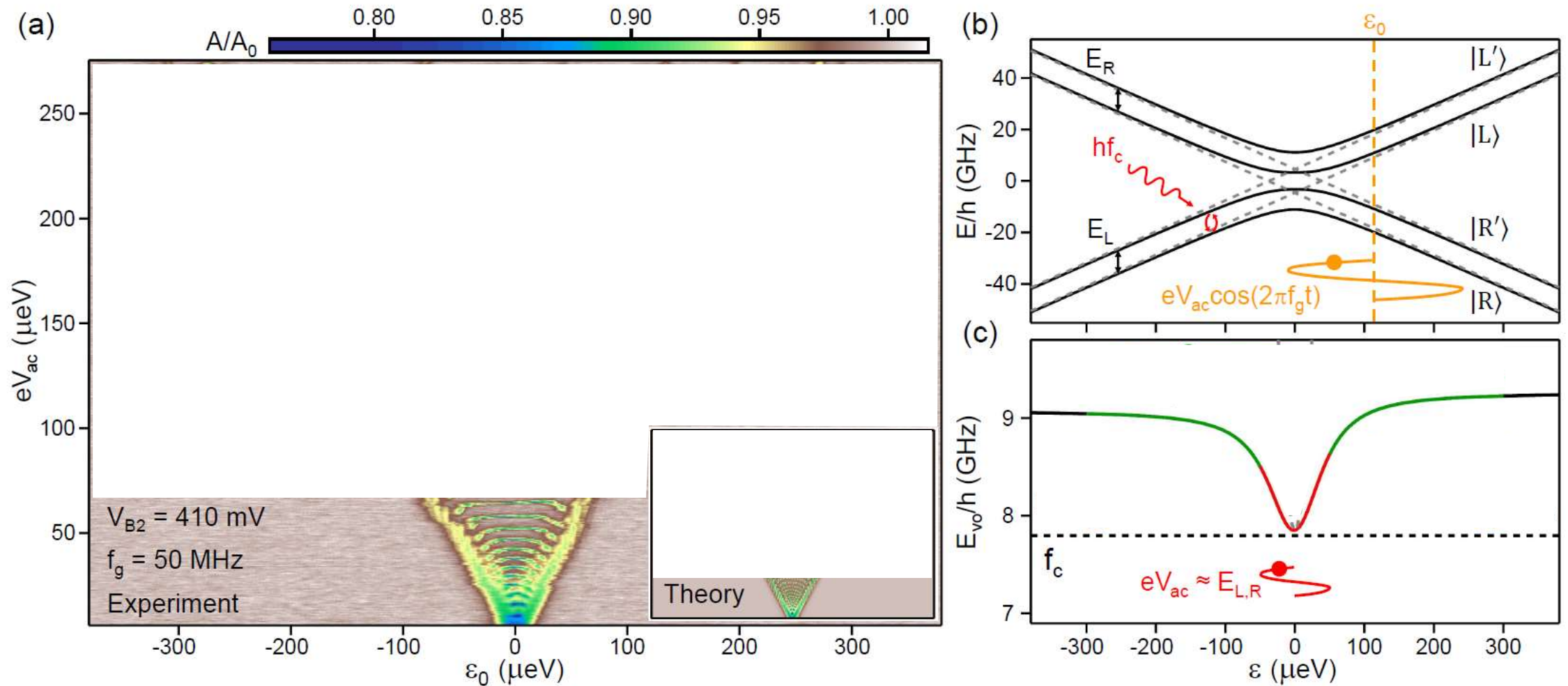
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Landau-Zehner-Stückelberg-Majorana Interferometry



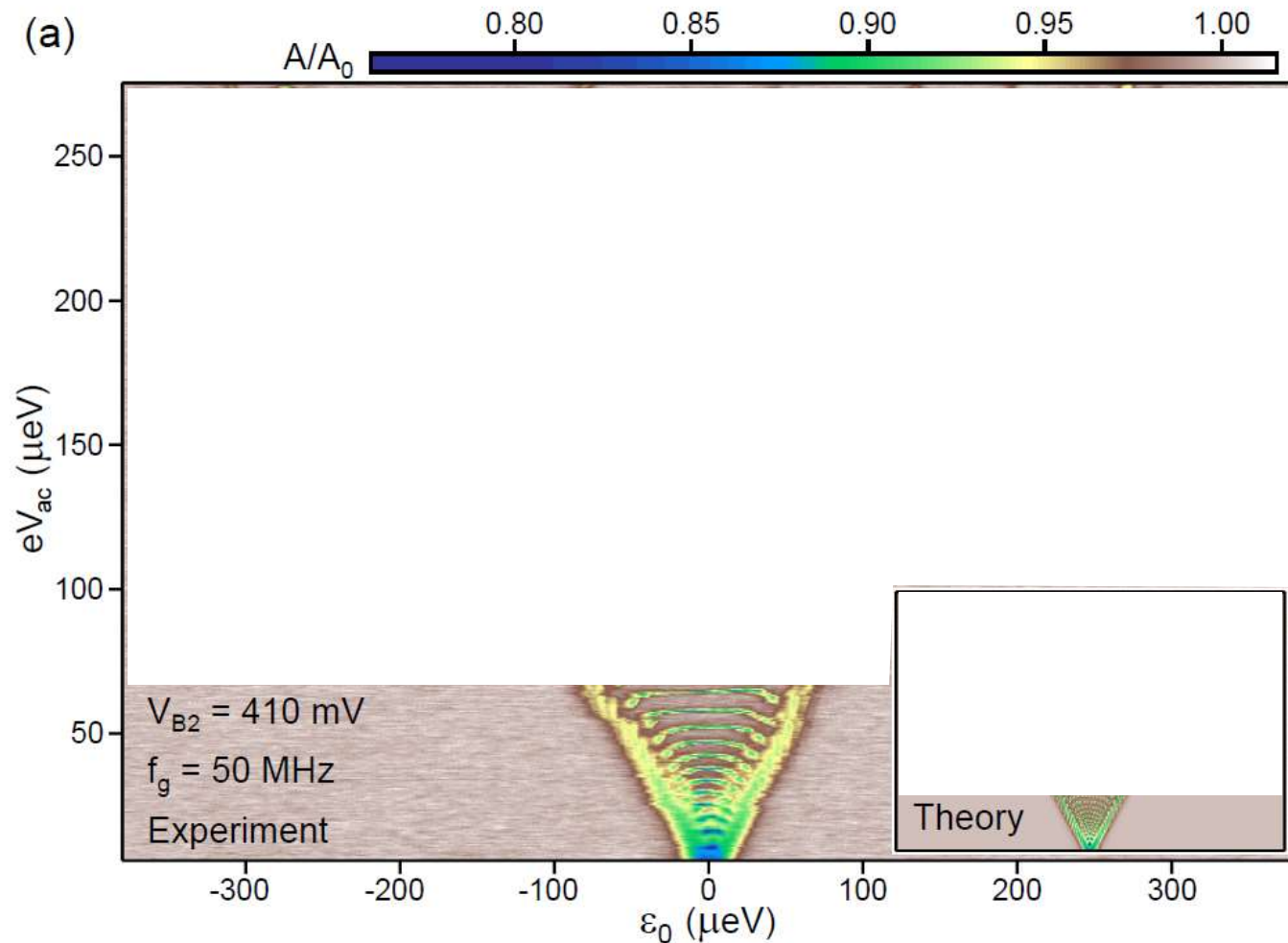
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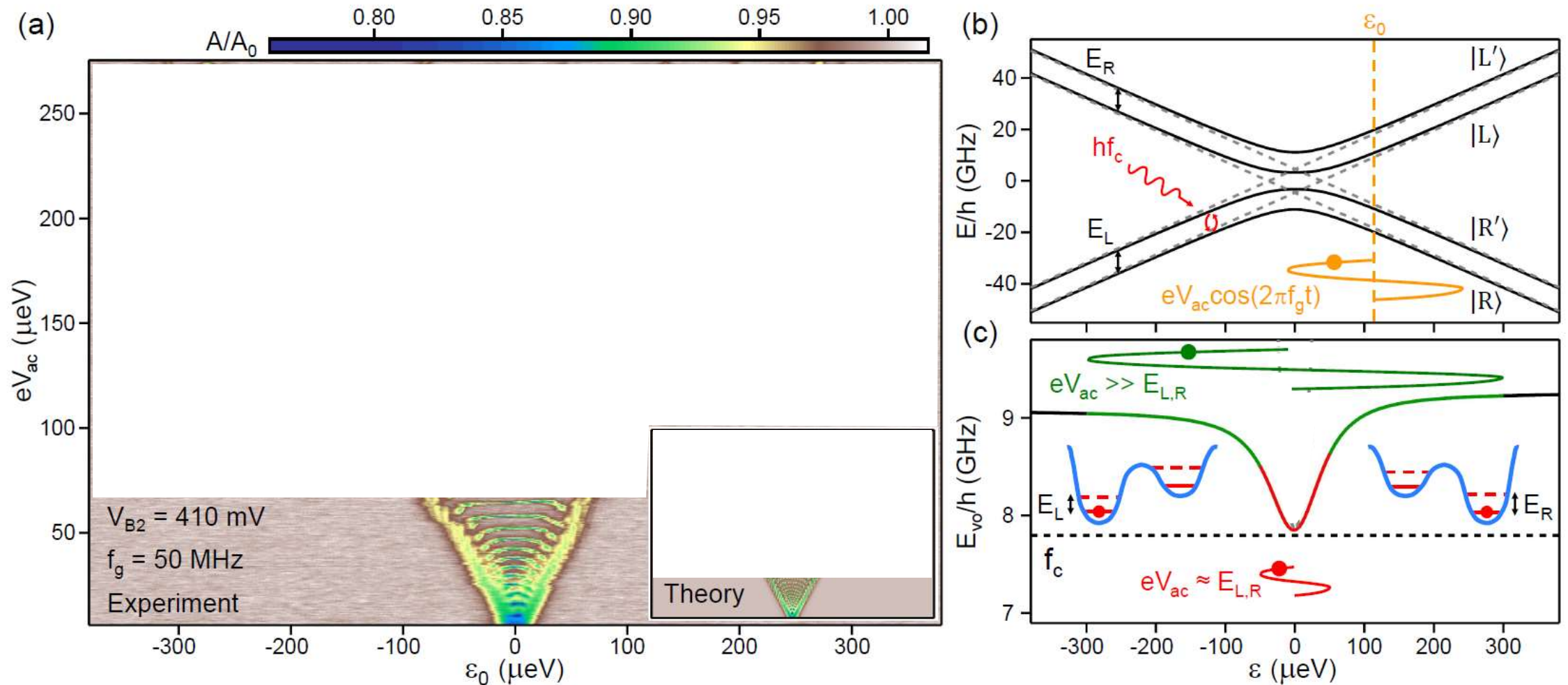
Landau-Zehner-Stückelberg-Majorana Interferometry



- for small detuning $|\varepsilon| \leq E_{L, R}$
 - hybridized valley-orbit states
- LZSM pattern resembles case of conventional two level system

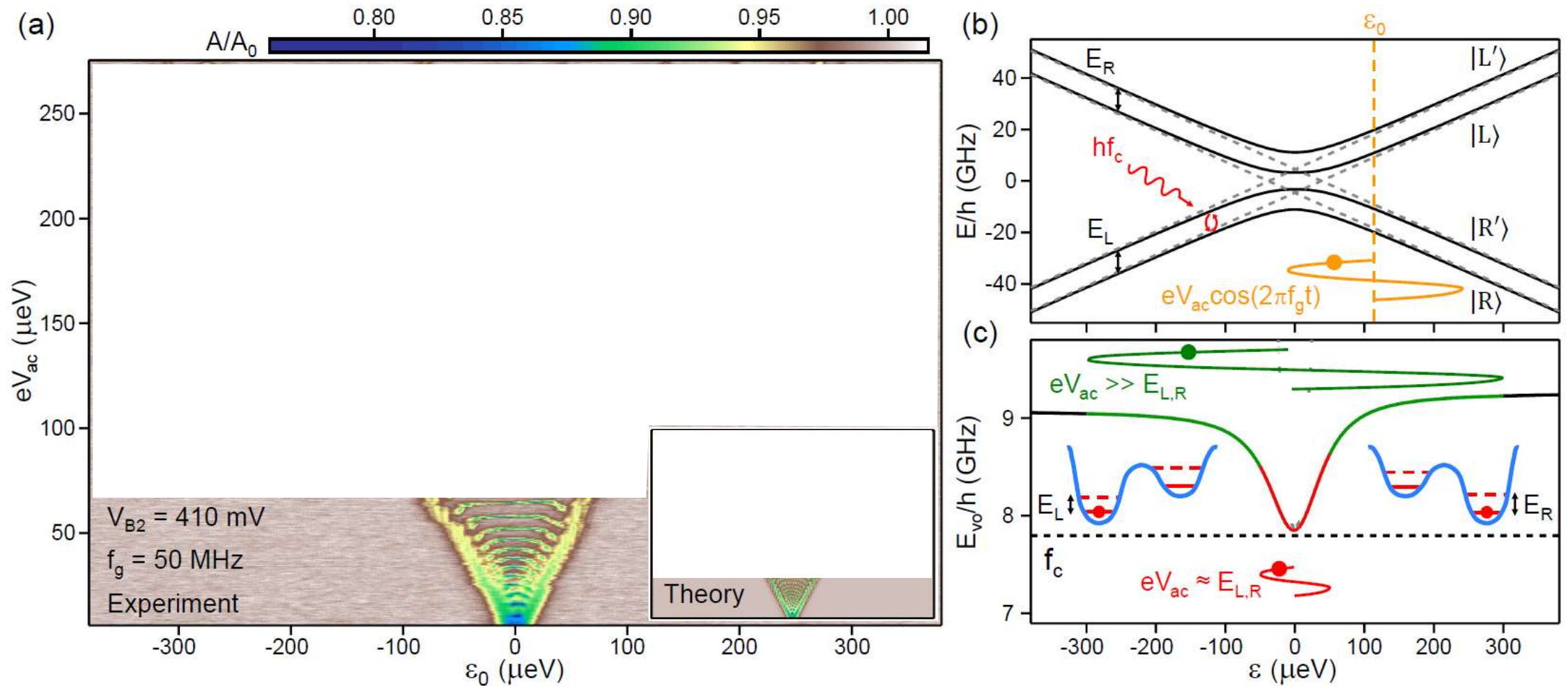
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Landau-Zehner-Stückelberg-Majorana Interferometry



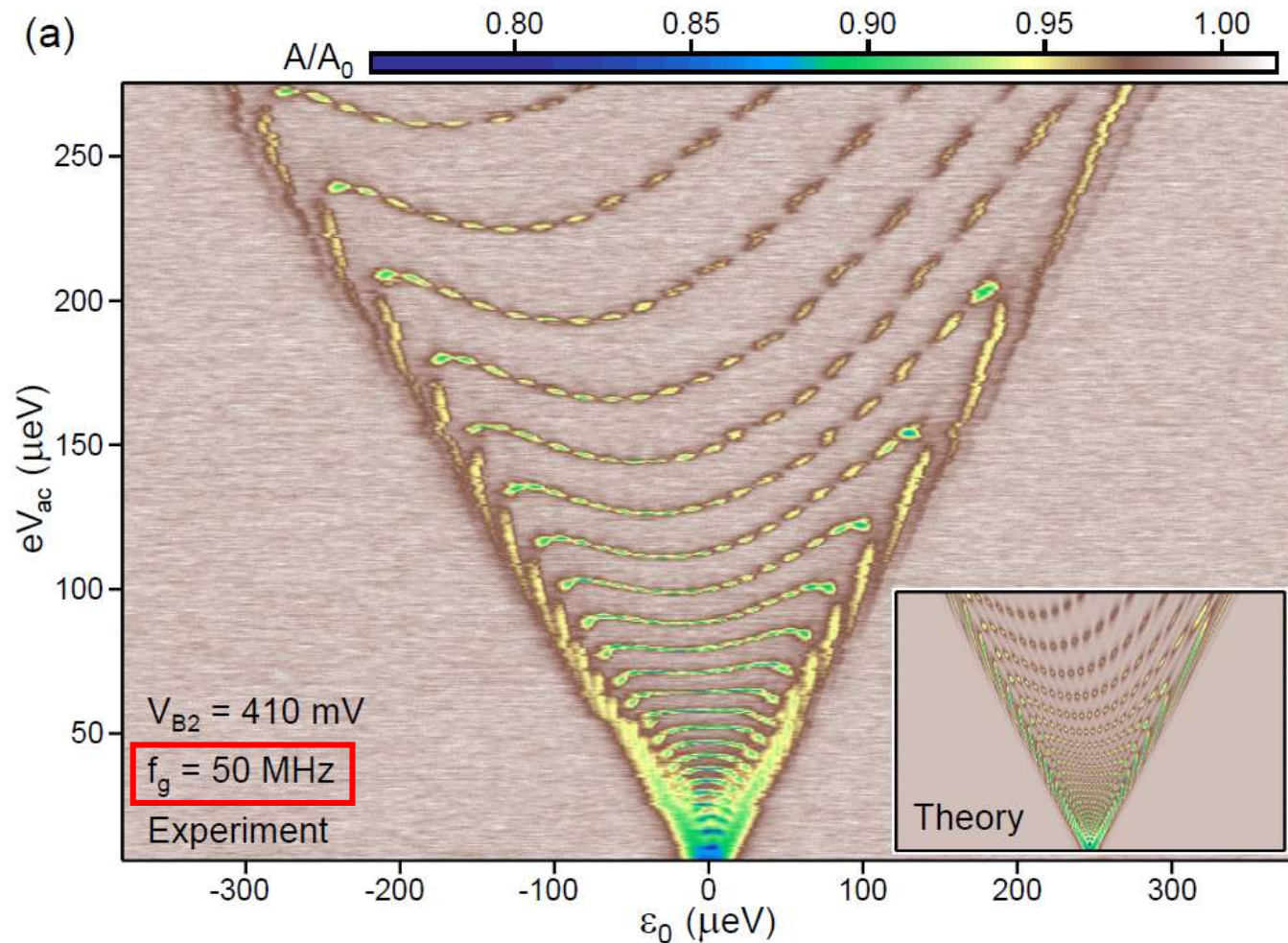
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Landau-Zehner-Stückelberg-Majorana Interferometry



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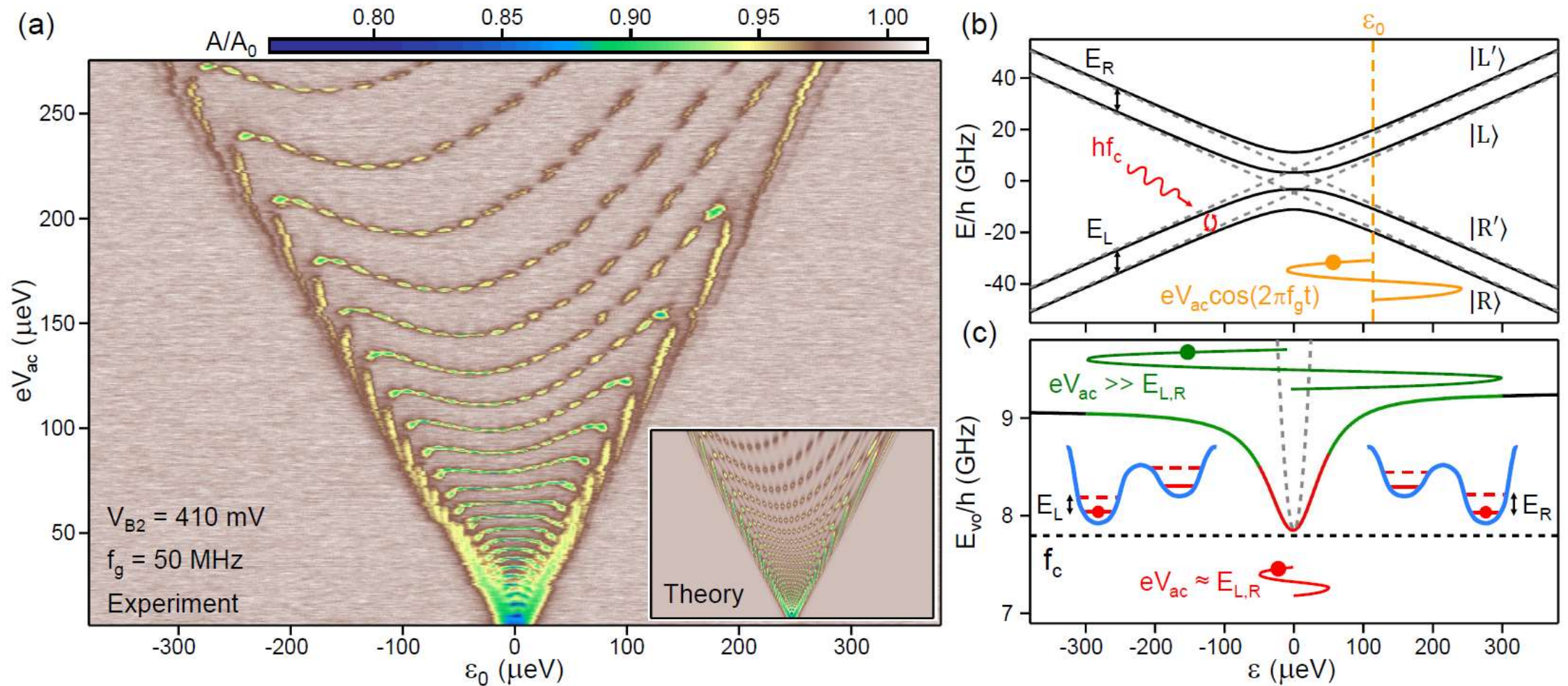


- at large detuning $|\varepsilon| \gg E_{L, R}$
 - single-dot valley splitting dominates
 - leads to asymmetric interference pattern
- long charge coherence
 - due to flat dispersion relation of valley-orbit qubit

$$\left| \frac{dE_{VO}}{d\varepsilon} \right| < 0.08$$
$$\left| \frac{dE_{CQ}}{d\varepsilon} \right| \approx 1$$

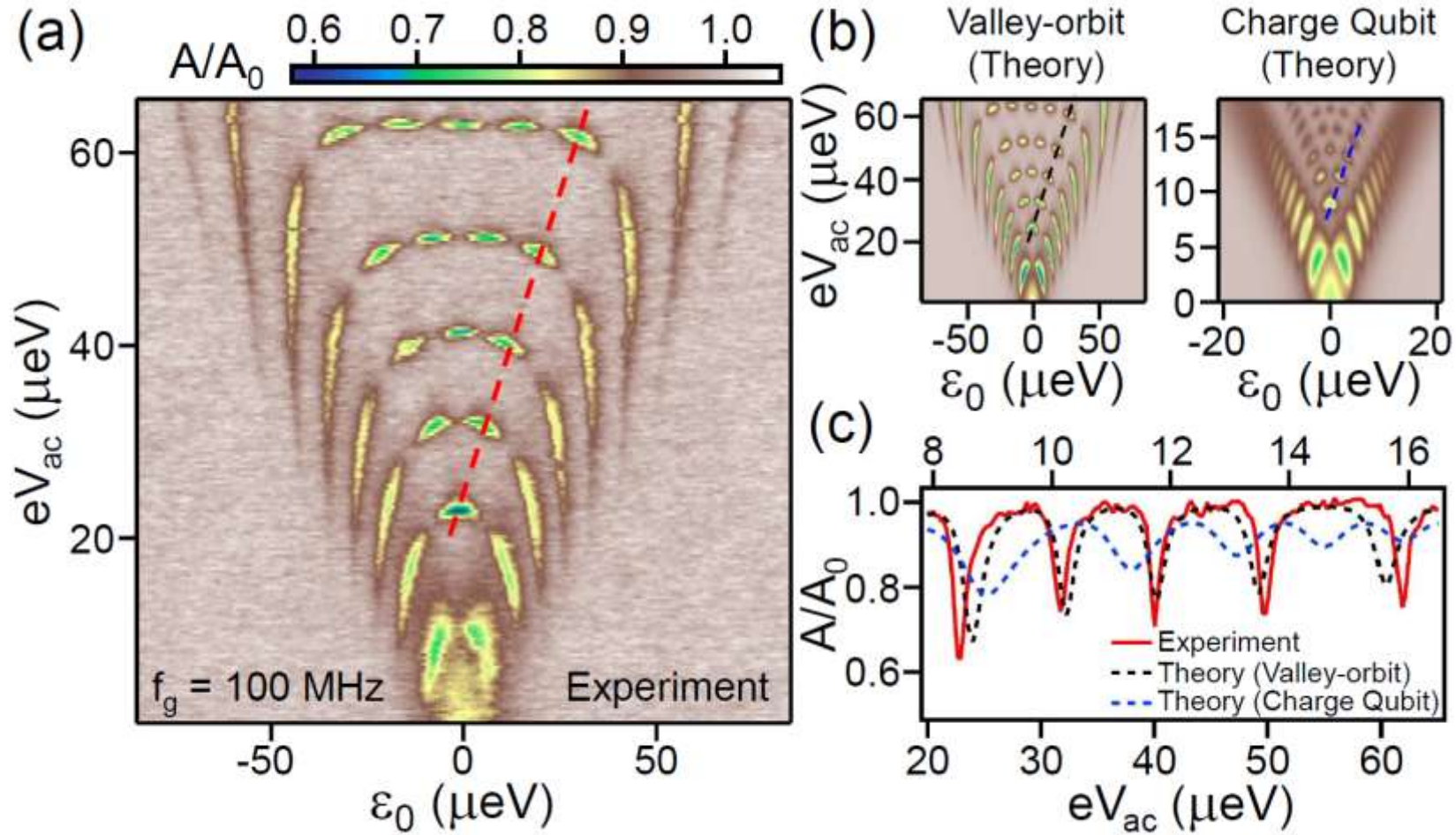
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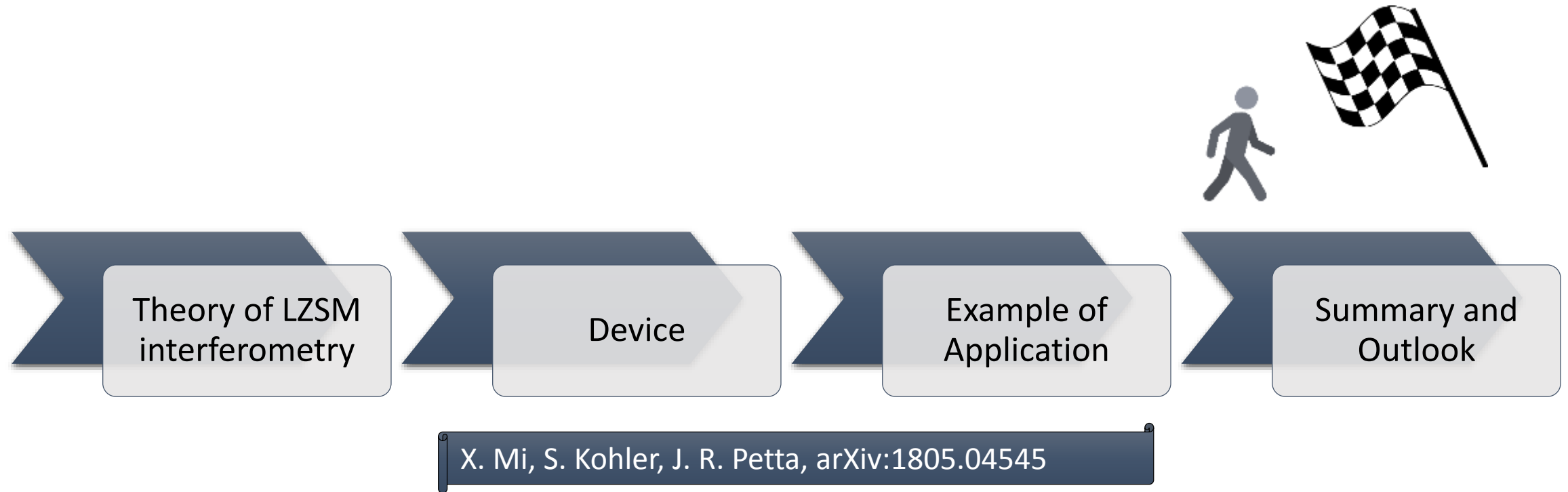
[1] Mi, X., Kohler, S., Petta, J. R., arXiv:1805.04545

Valley-Orbit Qubit Advantage



[1] Mi, X., Kohler, S., Petta, J. R., arXiv:1805.04545

Outline



Summary and Outlook

- Landau-Zehner-Stückelberg-Majorana Interferometry
 - allows determination of important parameters of Hamiltonian
- LZSM interference pattern in Si/SiGe DQD
 - very low driving frequency of 50 MHz (compared to GHz in other systems)
- valley-orbit qubit less sensitive to charge noise
 - use valley degree of freedom for enhanced silicon qubits?
 - deterministic tailoring of valley splitting necessary

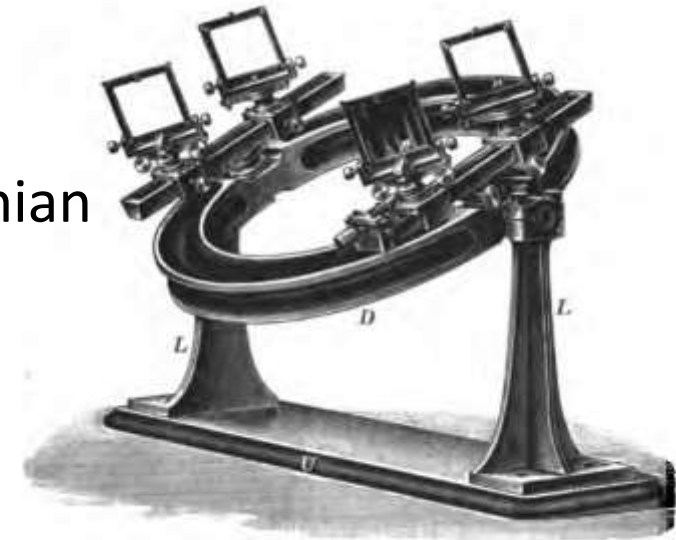
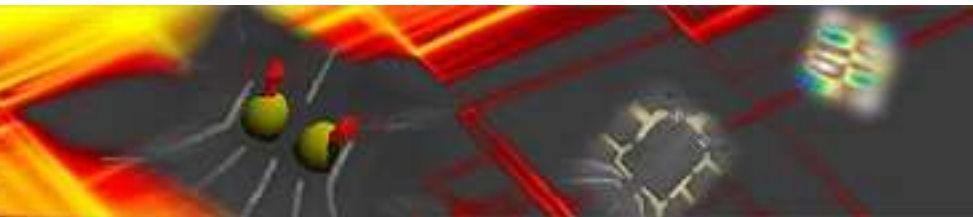


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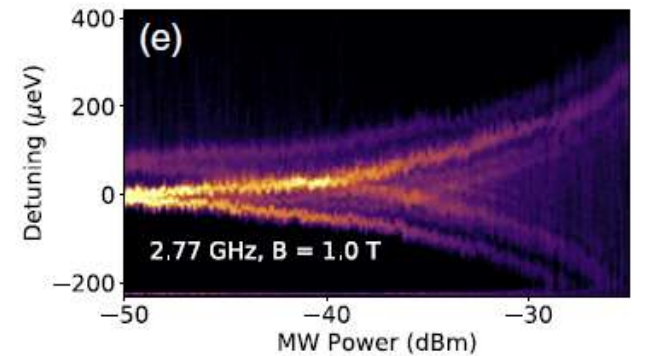
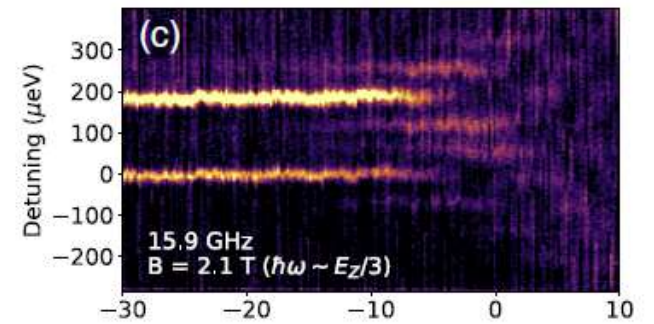
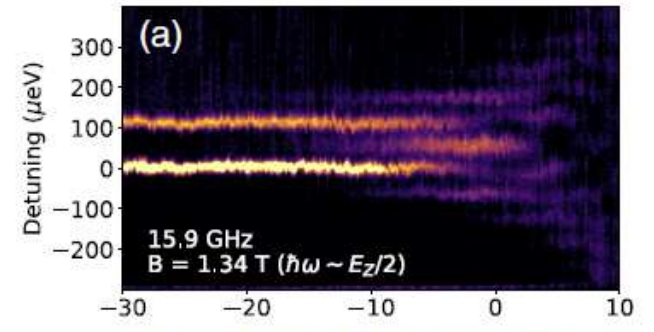
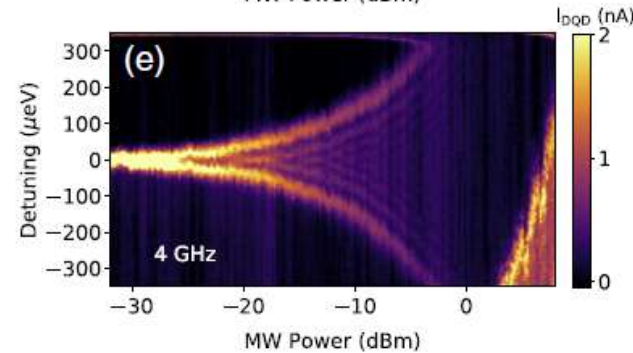
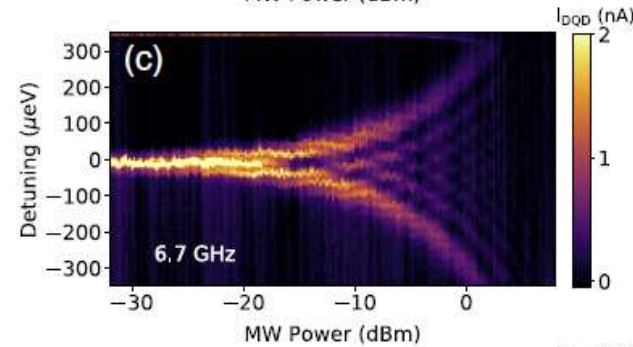
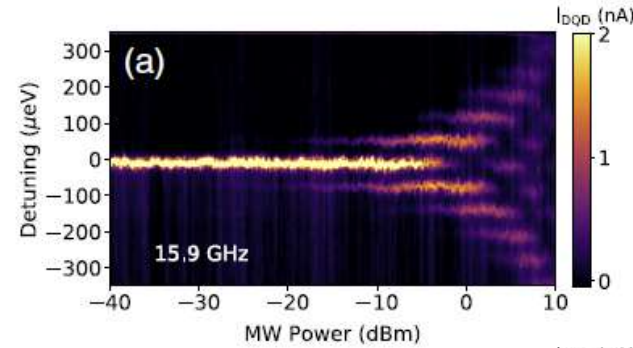
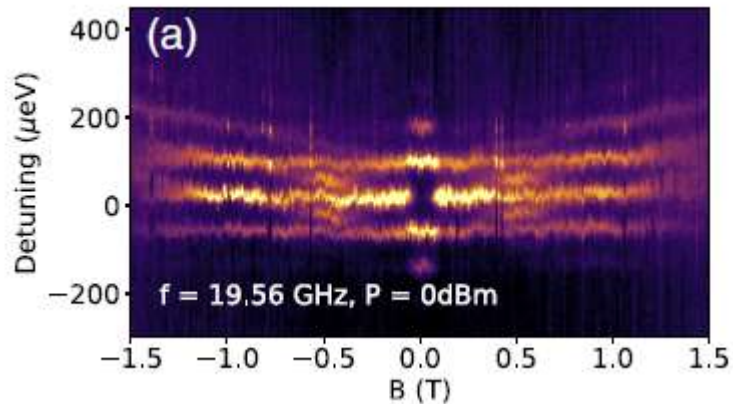
Additional Slides

- LZSM interferometry of Single Hole in GaAs



LZSM Interferometry of Single Hole in GaAs

- Single hole in GaAs DQD
- strong SOI
- two tunneling processes
 - spin conserving
 - spin flipping



[1] A. Bogan *et al.*, PRL **120**, 207701 (2018)